Electronic Supplementary Material (ESI) for RSC Advances.

Supplementary Information

First-principles study on electronic states of In_2Se_3/Au heterostructure controlled by strain engineering

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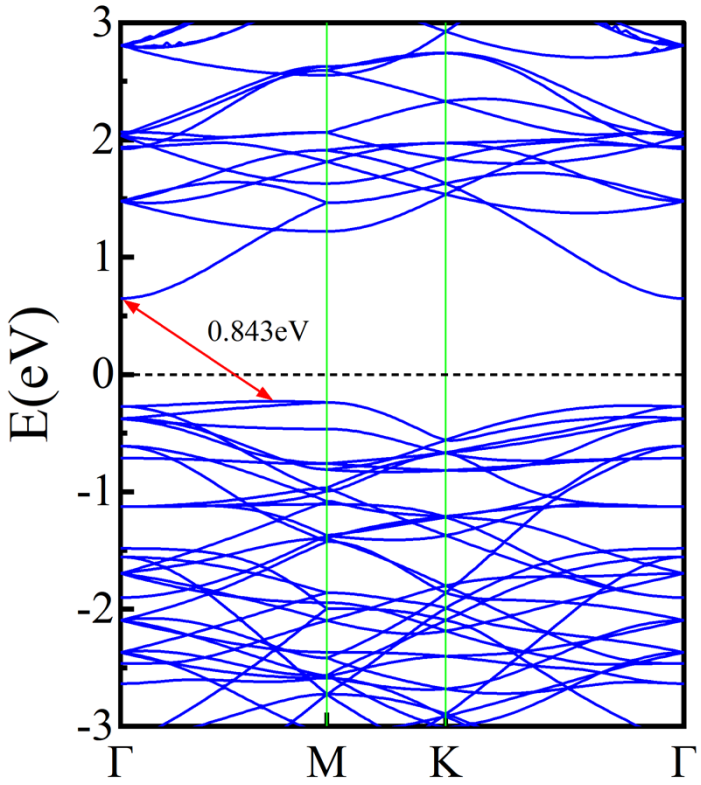

Figure. S1. Band structure of monolayer In_2Se_3. The Fermi level is set to zero energy and is denoted by the dashed line.

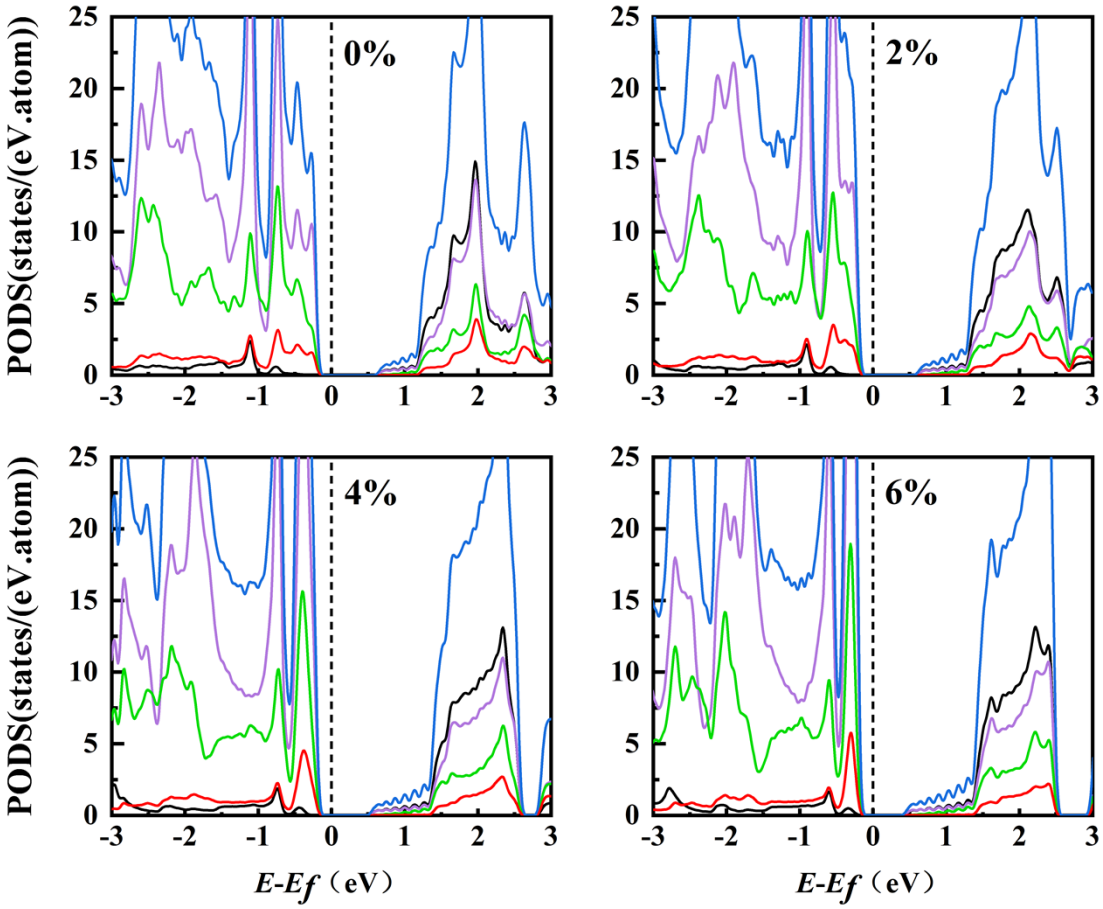

Figure. S2. Partial density of states (PDOS) of In_2Se_3 under biaxial tensile strain. The black, purple, green, red and blue lines represent the In s, In p, Se s, Se p and the total density of states, respectively. The black vertical dashed line represents Fermi level.